



# 300-MHz to 4-GHz Quadrature Modulator

Check for Samples: TRF3705

#### **FEATURES**

- **High Linearity:** 
  - Output IP3: 30 dBm at 1850 MHz
- Low Output Noise Floor: -160 dBm/Hz
- 78-dBc Single-Carrier WCDMA ACPR at -10-dBm Channel Power
- Unadjusted Carrier Suppression: -40 dBm
- Unadjusted Sideband Suppression: -45 dBc
- Single Supply: 3.3-V Operation
- 1-bit Gain Step Control
- Fast Power-Up/Power-Down

# **APPLICATIONS**

- **Cellular Base Station Transmitter**
- CDMA: IS95, UMTS, CDMA2000, TD-SCDMA
- LTE (Long Term Evolution)
- TDMA: GSM, EDGE/UWC-136
- **Multicarrier GSM (MC-GSM)**
- Wireless MAN Wideband Transceivers

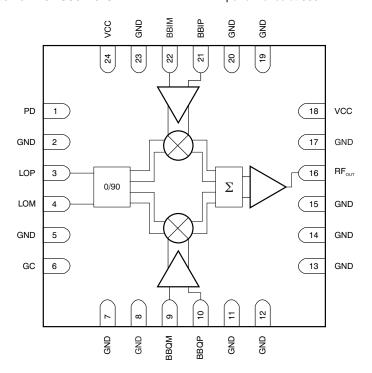
#### DESCRIPTION

The TRF3705 is a low-noise direct quadrature modulator, capable of converting complex modulated signals from baseband or IF directly up to RF. The TRF3705 is a high-performance, superior-linearity device that is ideal to up-convert to RF frequencies of 300 MHz<sup>(1)</sup> through 4 GHz. The modulator is implemented as a double-balanced mixer.

The output block consists differential-to-single-ended converter that is capable of driving a single-ended 50- $\Omega$  load. The TRF3705 requires a 0.25-V common-mode voltage for optimum linearity performance. The TRF3705 also provides a fast power-down pin that can be used to reduce power dissipation in TDD applications.

The TRF3705 is available in an RGE-24 VQFN package.

(1) Appropriate matching network is required for optimal performance at 300 MHz.



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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

## AVAILABLE DEVICE OPTIONS(1)

PRODUCT	PACKAGE- LEAD	PACKAGE DESIGNATOR	SPECIFIED TEMPERATURE RANGE	PACKAGE MARKING	ORDERING NUMBER	TRANSPORT MEDIA, QUANTITY
TDF2705	RGE-24	RGE	40°C to 105°C	TDF270FIDCF	TRF3705IRGET	Tape and Reel, 250
TRF3705	RGE-24	RGE	–40°C to +85°C	TRF3705IRGE	TRF3705IRGER	Tape and Reel, 3000

<sup>(1)</sup> For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the device product folder at www.ti.com.

# **ABSOLUTE MAXIMUM RATINGS**(1)

Over operating free-air temperature range (unless otherwise noted).

		VALUE	UNIT
Supply voltage	range <sup>(2)</sup>	-0.3 to +6	V
Digital I/O voltage range		-0.3 to V <sub>CC</sub> +0.5	V
Operating virtual junction temperature range, T <sub>J</sub>		-40 to +150	°C
Operating ambient temperature range, T <sub>A</sub> —40 to +85		°C	
Storage temper	rature range, T <sub>stg</sub>	-65 to +150	°C
	Human body model, HBM	4000	V
ESD ratings	Charged device model, CDM	250	V
	Machine model, MM	200	V

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### RECOMMENDED OPERATING CONDITIONS

Over operating free-air temperature range (unless otherwise noted).

			J (	,					
						MIN	NOM	MAX	UNIT
$V_{CC}$	Power-supply vo	ltage				3.15	3.3	3.6	V

#### THERMAL CHARACTERISTICS

Over recommended operating free-air temperature range (unless otherwise noted).

	PARAMETER <sup>(1)</sup>	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$R_{\theta JA}$	Thermal resistance, junction-to-ambient	High-K board, still air		29.4		°C/W
$R_{\thetaJC}$	Thermal resistance, junction-to-board			18.6		°C/W

(1) Determined using JEDEC standard JESD-51 with high-K board

<sup>(2)</sup> All voltage values are with respect to network ground terminal.



#### THERMAL INFORMATION

		TRF3705		
	THERMAL METRIC <sup>(1)</sup>	RGE (VQFN)	UNITS	
		24 PINS		
$\theta_{JA}$	Junction-to-ambient thermal resistance	38.4		
$\theta_{\text{JCtop}}$	Junction-to-case (top) thermal resistance	42.5		
$\theta_{JB}$	Junction-to-board thermal resistance	16.6	°C/M	
Ψлт	Junction-to-top characterization parameter	0.9	°C/W	
ΨЈВ	Junction-to-board characterization parameter	16.6		
$\theta_{JCbot}$	Junction-to-case (bottom) thermal resistance	6.6		

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

#### **ELECTRICAL CHARACTERISTICS: GENERAL**

Over recommended operating conditions; at power supply = 3.3 V and T<sub>A</sub> = +25°C, unless otherwise noted.

	PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNIT
DC PAR	AMETERS				'	
	Tatal avantu avant	T <sub>A</sub> = +25°C, device on (PD = low)		306		mA
I <sub>CC</sub>	Total supply current	T <sub>A</sub> = +25°C, device off (PD = high)		35		μA
LO INPL	JT				•	
	LO low frequency			300		MHz
$f_{LO}$	LO high frequency			4000		MHz
	LO input power		-10	0	+15	dBm
BASEBA	AND INPUTS					
V <sub>CM</sub>	I and Q input dc common-mode voltage			0.25 0.5		V
BW	1-dB input frequency bandwidth			1000		MHz
7	Innut impadance	Resistance		8		kΩ
Z <sub>I</sub>	Input impedance	Parallel capacitance		4.6		pF
POWER	ON/OFF					
	Turn on time	PD = low to 90% final output power		0.2		μs
	Turn off time	PD = high to initial output power –30 dB		0.2		μs
DIGITAL	. INTERFACE					
V <sub>IH</sub>	PD high-level input voltage		2			V
V <sub>IL</sub>	PD low-level input voltage				0.8	V

Product Folder Link(s): TRF3705



# **ELECTRICAL CHARACTERISTICS**

Over recommended operating conditions; at power supply = 3.3 V,  $T_A$  = +25°C,  $V_{CM}$  = 0.25 V; LO Power = 0 dBm, single-ended (LOP); GC set low,  $V_{IN}$  BB = 1.0  $V_{PP}$  (diff) in quadrature, and  $f_{BB}$  = 5.5 MHz, standard broadband output matching circuit, unless otherwise noted.

	PARAMETERS	TEST CONDITIONS	MIN TYP MAX	UNIT
f <sub>LO</sub> = 400 I	MHz			
G	Voltage gain	Output RMS voltage over input I (or Q) RMS voltage, GC set low	-4.7	dB
G	Voltage gain	Output RMS voltage over input I (or Q) RMS voltage, GC set high	-1.9	dB
Б.	0.1.1	GC set low	-0.7	dBm
P <sub>OUT</sub>	Output power	GC set high	2.1	dBm
D. 1D		GC set low	8.5	dBm
P1dB	Output compression point	GC set high	9.1	dBm
IDO	0.1.1100	f <sub>BB1</sub> = 4.5 MHz; f <sub>BB2</sub> = 5.5 MHz; GC set low	26.0	dBm
IP3	Output IP3	f <sub>BB1</sub> = 4.5 MHz; f <sub>BB2</sub> = 5.5 MHz; GC set high	25.4	dBm
IDO	0.1.1100	Measured at f <sub>LO</sub> + (f <sub>BB1</sub> ± f <sub>BB2</sub> ), GC set low	60.2	dBm
IP2	Output IP2	Measured at f <sub>LO</sub> + (f <sub>BB1</sub> ± f <sub>BB2</sub> ), GC set high	61.9	dBm
SBS	Unadjusted sideband suppression		-57.4	dBc
		Measured at LO frequency	<b>–</b> 51.6	dBm
DF	Unadjusted carrier feedthrough	Measured at 2 ● LO	<b>–</b> 50	dBm
		Measured at 3 ● LO	-49	dBm
	Output noise floor	DC only to BB inputs; 10-MHz offset from LO	-166.7	dBm/Hz
HD2 <sub>BB</sub>	Baseband harmonics	Measured with $\pm 1$ -MHz tone at 0.5 V <sub>PP</sub> each at $f_{LO} \pm (2 \bullet f_{BB})$	-67	dBc
HD3 <sub>BB</sub>	Baseband harmonics	Measured with $\pm 1$ -MHz tone at 0.5 V <sub>PP</sub> each at $f_{LO} \pm (3 \bullet f_{BB})$	-64	dBc
f <sub>LO</sub> = 750 I	MHz			
0		Output RMS voltage over input I (or Q) RMS voltage, GC set low	0.2	dB
G	Voltage gain	Output RMS voltage over input I (or Q) RMS voltage, GC set high	3.0	dB
D	Output naves	GC set low	4.2	dBm
P <sub>OUT</sub>	Output power	GC set high	7.0	dBm
D4 -ID	0	GC set low	13.3	dBm
P1dB	Output compression point	GC set high	13.9	dBm
IP3	Output IP2	$f_{BB1}$ = 4.5 MHz; $f_{BB2}$ = 5.5 MHz; GC set low	31.5	dBm
1173	Output IP3	$f_{BB1} = 4.5 \text{ MHz}$ ; $f_{BB2} = 5.5 \text{ MHz}$ ; GC set high	30.8	dBm
IDO	Output ID2	Measured at f <sub>LO</sub> + (f <sub>BB1</sub> ± f <sub>BB2</sub> ), GC set low	73.6	dBm
IP2	Output IP2	Measured at f <sub>LO</sub> + (f <sub>BB1</sub> ± f <sub>BB2</sub> ), GC set high	80.5	dBm
SBS	Unadjusted sideband suppression		-45.2	dBc
		Measured at LO frequency	-45.7	dBm
CF	Unadjusted carrier feedthrough	Measured at 2 ● LO	-46	dBm
		Measured at 3 ◆ LO	-53.5	dBm
	Output noise floor	DC only to BB inputs; 10-MHz offset from LO	-159.9	dBm/Hz
HD2 <sub>BB</sub>	Baseband harmonics	Measured with $\pm 1$ -MHz tone at 0.5 V <sub>PP</sub> each at $f_{LO} \pm (2 \bullet f_{BB})$	-70	dBc
HD3 <sub>BB</sub>	Baseband harmonics	Measured with $\pm 1$ -MHz tone at 0.5 V <sub>PP</sub> each at $f_{LO} \pm (3 \bullet f_{BB})$	-66	dBc

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# **ELECTRICAL CHARACTERISTICS (continued)**

Over recommended operating conditions; at power supply = 3.3 V,  $T_A$  = +25°C,  $V_{CM}$  = 0.25 V; LO Power = 0 dBm, single-ended (LOP); GC set low,  $V_{IN}$  BB = 1.0  $V_{PP}$  (diff) in quadrature, and  $f_{BB}$  = 5.5 MHz, standard broadband output matching circuit, unless otherwise noted.

	PARAMETERS	TEST CONDITIONS	MIN TYP MAX	UNIT
f <sub>LO</sub> = 900	MHz			
G	Voltage gain	Output RMS voltage over input I (or Q) RMS voltage, GC set low	0.3	dB
G	Voltage gain	Output RMS voltage over input I (or Q) RMS voltage, GC set high	3.1	dB
<b>D</b>	0	GC set low	4.3	dBm
P <sub>OUT</sub>	Output power	GC set high	7.1	dBm
D4 ID	0.1.1	GC set low	13.2	dBm
P1dB	Output compression point	GC set high	13.7	dBm
ID0	0.1.1100	f <sub>BB1</sub> = 4.5 MHz; f <sub>BB2</sub> = 5.5 MHz; GC set low	31.7	dBm
IP3	Output IP3	f <sub>BB1</sub> = 4.5 MHz; f <sub>BB2</sub> = 5.5 MHz; GC set high	30.9	dBm
IDO	Outrant IDO	Measured at f <sub>LO</sub> + (f <sub>BB1</sub> ± f <sub>BB2</sub> ), GC set low	71.5	dBm
IP2	Output IP2	Measured at f <sub>LO</sub> + (f <sub>BB1</sub> ± f <sub>BB2</sub> ), GC set high	75.3	dBm
SBS	Unadjusted sideband suppression		-43.8	dBc
		Measured at LO frequency	-48.5	dBm
CF	Unadjusted carrier feedthrough	Measured at 2 ● LO	<b>-</b> 53	dBm
		Measured at 3 ● LO	<b>–</b> 50	dBm
	Output noise floor	DC only to BB inputs; 10-MHz offset from LO	-157.9	dBm/Hz
HD2 <sub>BB</sub>	Baseband harmonics	Measured with $\pm 1$ -MHz tone at 0.5 V <sub>PP</sub> each at $f_{LO} \pm (2 \bullet f_{BB})$	-80	dBc
HD3 <sub>BB</sub>	Baseband harmonics	Measured with $\pm 1$ -MHz tone at 0.5 V <sub>PP</sub> each at $f_{LO} \pm (3 \bullet f_{BB})$	-65	dBc
f <sub>LO</sub> = 1840	MHz			
0	Vallana nain	Output RMS voltage over input I (or Q) RMS voltage, GC set low	-0.1	dB
G	Voltage gain	Output RMS voltage over input I (or Q) RMS voltage, GC set high	2.5	dB
D	Output naves	GC set low	3.9	dBm
P <sub>OUT</sub>	Output power	GC set high	6.5	dBm
D4 -ID	0	GC set low	13.2	dBm
P1dB	Output compression point	GC set high	13.6	dBm
IP3	Output IP2	f <sub>BB1</sub> = 4.5 MHz; f <sub>BB2</sub> = 5.5 MHz; GC set low	32.1	dBm
IP3	Output IP3	f <sub>BB1</sub> = 4.5 MHz; f <sub>BB2</sub> = 5.5 MHz; GC set high	30.3	dBm
IP2	Output ID2	Measured at f <sub>LO</sub> + (f <sub>BB1</sub> ± f <sub>BB2</sub> ), GC set low	60.8	dBm
IFZ	Output IP2	Measured at f <sub>LO</sub> + (f <sub>BB1</sub> ± f <sub>BB2</sub> ), GC set high	62.0	dBm
SBS	Unadjusted sideband suppression		-43.4	dBc
		Measured at LO frequency	-42.4	dBm
CF	Unadjusted carrier feedthrough	Measured at 2 ● LO	-41	dBm
		Measured at 3 ● LO	<b>-53</b>	dBm
	Output noise floor	DC only to BB inputs; 10-MHz offset from LO	-158.8	dBm/Hz
HD2 <sub>BB</sub>	Baseband harmonics	Measured with $\pm 1$ -MHz tone at 0.5 V <sub>PP</sub> each at $f_{LO} \pm (2 \bullet f_{BB})$	-69	dBc
HD3 <sub>BB</sub>	Baseband harmonics	Measured with $\pm 1$ -MHz tone at 0.5 V <sub>PP</sub> each at $f_{LO} \pm (3 \bullet f_{BB})$	-80	dBc



# **ELECTRICAL CHARACTERISTICS (continued)**

Over recommended operating conditions; at power supply = 3.3 V,  $T_A$  = +25°C,  $V_{CM}$  = 0.25 V; LO Power = 0 dBm, single-ended (LOP); GC set low,  $V_{IN}$  BB = 1.0  $V_{PP}$  (diff) in quadrature, and  $f_{BB}$  = 5.5 MHz, standard broadband output matching circuit, unless otherwise noted.

	PARAMETERS	TEST CONDITIONS	MIN TYP MAX	UNIT
f <sub>LO</sub> = 2140	MHz			
G	Voltage gain	Output RMS voltage over input I (or Q) RMS voltage, GC set low	0.1	dB
G	Voltage gain	Output RMS voltage over input I (or Q) RMS voltage, GC set high	2.9	dB
D	0	GC set low	4.1	dBm
P <sub>OUT</sub>	Output power	GC set high	6.9	dBm
D4 -ID	0	GC set low	13.1	dBm
P1dB	Output compression point	GC set high	13.5	dBm
ID0	Outsid IDO	f <sub>BB1</sub> = 4.5 MHz; f <sub>BB2</sub> = 5.5 MHz; GC set low	28.6	dBm
IP3	Output IP3	f <sub>BB1</sub> = 4.5 MHz; f <sub>BB2</sub> = 5.5 MHz; GC set high	27.6	dBm
IDO	Outsid IDO	Measured at f <sub>LO</sub> + (f <sub>BB1</sub> ± f <sub>BB2</sub> ), GC set low	65.5	dBm
IP2	Output IP2	Measured at f <sub>LO</sub> + (f <sub>BB1</sub> ± f <sub>BB2</sub> ), GC set high	68.2	dBm
SBS	Unadjusted sideband suppression		-45.6	dBc
		Measured at LO frequency	-39.3	dBm
CF	Unadjusted carrier feedthrough	Measured at 2 ● LO	-37	dBm
		Measured at 3 ● LO	-46	dBm
	Output noise floor	DC only to BB inputs; 10-MHz offset from LO	-160.0	dBm/Hz
HD2 <sub>BB</sub>	Baseband harmonics	Measured with $\pm 1$ -MHz tone at 0.5 V <sub>PP</sub> each at $f_{LO} \pm (2 \bullet f_{BB})$	-61	dBc
HD3 <sub>BB</sub>	Baseband harmonics	Measured with $\pm 1$ -MHz tone at 0.5 V <sub>PP</sub> each at $f_{LO} \pm (3 \bullet f_{BB})$ —60		dBc
f <sub>LO</sub> = 2600	MHz			
0	Valta and main	Output RMS voltage over input I (or Q) RMS voltage, GC set low	-0.8	dB
G	Voltage gain	Output RMS voltage over input I (or Q) RMS voltage, GC set high	2.0	dB
D	Output nouse	GC set low	3.2	dBm
P <sub>OUT</sub>	Output power	GC set high	5.6	dBm
D4 -ID	0	GC set low	12.5	dBm
P1dB	Output compression point	GC set high	12.8	dBm
IDO	Outset ID2	f <sub>BB1</sub> = 4.5 MHz; f <sub>BB2</sub> = 5.5 MHz; GC set low	28.0	dBm
IP3	Output IP3	Ff <sub>BB1</sub> = 4.5 MHz; f <sub>BB2</sub> = 5.5 MHz; GC set high	27.2	dBm
IDO	Outsid IDO	Measured at f <sub>LO</sub> + (f <sub>BB1</sub> ± f <sub>BB2</sub> ), GC set low	67.9	dBm
IP2	Output IP2	Measured at f <sub>LO</sub> + (f <sub>BB1</sub> ± f <sub>BB2</sub> ), GC set high	66.4	dBm
SBS	Unadjusted sideband suppression		<b>-</b> 52.9	dBm
		Measured at LO frequency	-37.8	dBm
CF	Unadjusted carrier feedthrough	Measured at 2 ● LO	<b>-41</b>	dBm
		Measured at 3 ● LO	-42	dBm
	Output noise floor	DC only to BB inputs; 10-MHz offset from LO	-160.6	dBm/Hz
HD2 <sub>BB</sub>	Baseband harmonics	Measured with $\pm 1$ -MHz tone at 0.5 V <sub>PP</sub> each at $f_{LO} \pm (2 \bullet f_{BB})$	-67	dBc
HD3 <sub>BB</sub>	Baseband harmonics	Measured with $\pm 1$ -MHz tone at 0.5 V <sub>PP</sub> each at $f_{LO} \pm (3 \bullet f_{BB})$	<b>–</b> 59	dBc

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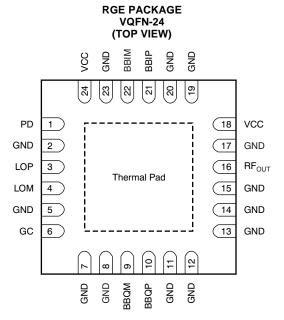
# **ELECTRICAL CHARACTERISTICS (continued)**

Over recommended operating conditions; at power supply = 3.3 V,  $T_A$  = +25°C,  $V_{CM}$  = 0.25 V; LO Power = 0 dBm, single-ended (LOP); GC set low,  $V_{IN}$  BB = 1.0  $V_{PP}$  (diff) in quadrature, and  $f_{BB}$  = 5.5 MHz, standard broadband output matching circuit, unless otherwise noted.

	PARAMETERS	TEST CONDITIONS	MIN TYP	MAX	UNIT				
f <sub>LO</sub> = 3500	o = 3500 MHz								
0	Valla na nain	Output RMS voltage over input I (or Q) RMS voltage, GC set low	-1.0		dB				
G	Voltage gain	Output RMS voltage over input I (or Q) RMS voltage, GC set high	1.8		dB				
Б	Output manua	GC set low	3.0		dBm				
P <sub>OUT</sub>	Output power	GC set high	5.8		dBm				
D14D	Outrout communication and	GC set low	12.1		dBm				
P1dB	Output compression point	GC set high	12.3		dBm				
IP3	Output ID2	f <sub>BB1</sub> = 4.5 MHz; f <sub>BB2</sub> = 5.5 MHz; GC set low	23.8		dBm				
IP3	Output IP3	f <sub>BB1</sub> = 4.5 MHz; f <sub>BB2</sub> = 5.5 MHz; GC set high	25.3		dBm				
IP2	Output ID2	Measured at f <sub>LO</sub> + (f <sub>BB1</sub> ± f <sub>BB2</sub> ), GC set low	47.8		dBm				
IP2	Output IP2	Measured at f <sub>LO</sub> + (f <sub>BB1</sub> ± f <sub>BB2</sub> ), GC set high	48.6		dBm				
SBS	Unadjusted sideband suppression		-45.2		dBm				
		Measured at LO frequency	-31.6		dBm				
CF	Unadjusted carrier feedthrough	Measured at 2 ◆ LO	-30		dBm				
		Measured at 3 ● LO	<b>-</b> 53		dBm				
	Output noise floor	DC only to BB inputs; 10-MHz offset from LO	-160.6		dBm/Hz				
HD2 <sub>BB</sub>	Baseband harmonics	Measured with ±1-MHz tone at 0.5 V <sub>PP</sub> each at f <sub>LO</sub> ±(2 ● f <sub>BB</sub> )	-54		dBc				
HD3 <sub>BB</sub>	Baseband harmonics	Measured with $\pm 1$ -MHz tone at 0.5 V <sub>PP</sub> each at $f_{LO} \pm (3 \bullet f_{BB})$	-50		dBc				



## **DEVICE INFORMATION**



#### **PIN FUNCTIONS**

	PIN	1/0	DESCRIPTION				
NO.	NAME	1/0	DESCRIPTION				
1	PD	I	Power-down digital input (high = device off)				
2	GND	I	Ground				
3	LOP	I	Local oscillator input				
4	LOM	I	Local oscillator input				
5	GND	I	und				
6	GC	I	n control digital input (high = high gain)				
7	GND	_	Ground or leave unconnected				
8	GND	I	Ground				
9	BBQM	I	In-quadrature input				
10	BBQP	I	In-quadrature input				
11	GND	I	Ground				
12	GND	I	Ground				
13	GND	I	Ground				
14	GND	I	Ground				
15	GND	I	Ground				
16	RF <sub>OUT</sub>	0	RF output				
17	GND	I	Ground				
18	VCC	I	Power supply				
19	GND	I	Ground				
20	GND	I	Ground				
21	BBIP	I	In-phase input				
22	BBIM	1	In-phase input				
23	GND	I	Ground				
24	VCC	I	Power supply				



# TYPICAL CHARACTERISTICS: Single-Tone Baseband

 $V_{CC} = 3.3 \text{ V}$ ;  $T_A = +25^{\circ}\text{C}$ ; LO = 0 dBm, single-ended drive (LOP); I/Q frequency ( $f_{BB}$ ) = 5.5 MHz; baseband I/Q amplitude =  $1-V_{PP}$  differential sine waves in quadrature with  $V_{CM} = 0.25 \text{ V}$ ; and broadband output match, unless otherwise noted.

#### OUTPUT POWER vs LO FREQUENCY (fLO) AND **TEMPERATURE** 10 $T_A = -40$ °C 9 $T_A = 25^{\circ}C$ 8 $T_A = 85^{\circ}C$ 7 6 5 4 3 2 1 0 -1 -2 500 1000 1500 2000 2500 3000 3500 4000 Frequency (MHz) Figure 1.

# OUTPUT POWER vs LO FREQUENCY (f<sub>LO</sub>) AND SUPPLY VOLTAGE

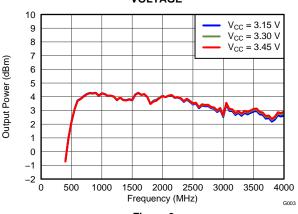
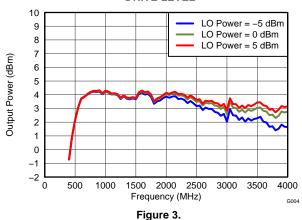


Figure 2.

# OUTPUT POWER vs LO FREQUENCY ( $f_{LO}$ ) OVER LO DRIVE LEVEL



OUTPUT POWER vs LO FREQUENCY ( $f_{LO}$ ) AND GAIN SELECT SETTING

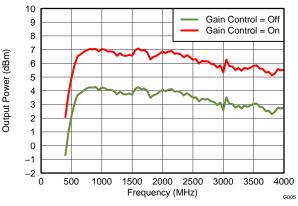
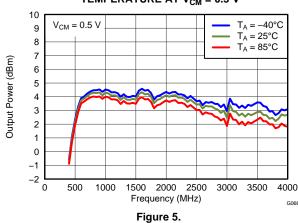


Figure 4.

# OUTPUT POWER vs LO FREQUENCY ( $f_{LO}$ ) AND TEMPERATURE AT $V_{CM} = 0.5 \text{ V}$



#### **OUTPUT POWER vs BASEBAND VOLTAGE AT 2140 MHz**

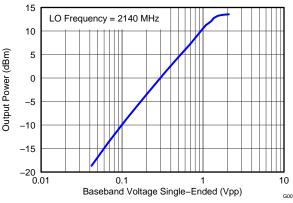
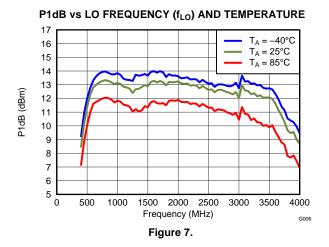
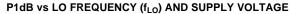


Figure 6.



 $V_{CC} = 3.3 \text{ V}; T_A = +25 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive (LOP)}; I/Q \text{ frequency (f}_{BB}) = 5.5 \text{ MHz}; \text{ baseband I/Q amplitude} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive (LOP)}; I/Q \text{ frequency (f}_{BB}) = 5.5 \text{ MHz}; \text{ baseband I/Q amplitude} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive (LOP)}; I/Q \text{ frequency (f}_{BB}) = 5.5 \text{ MHz}; \text{ baseband I/Q amplitude} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive (LOP)}; I/Q \text{ frequency (f}_{BB}) = 5.5 \text{ MHz}; \text{ baseband I/Q amplitude} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive (LOP)}; I/Q \text{ frequency (f}_{BB}) = 5.5 \text{ MHz}; \text{ baseband I/Q amplitude} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive} = 1.0 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-end$  $1-V_{PP}$  differential sine waves in quadrature with  $V_{CM} = 0.25$  V; and broadband output match, unless otherwise noted.





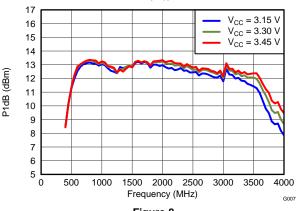
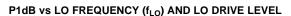
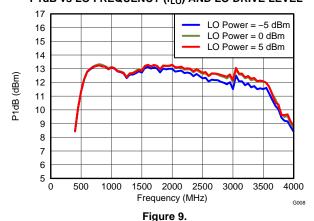
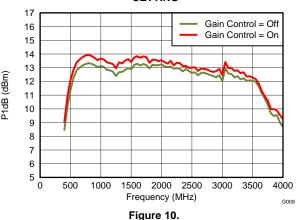


Figure 8.





P1dB vs LO FREQUENCY (fLO) AND GAIN SELECT SETTING



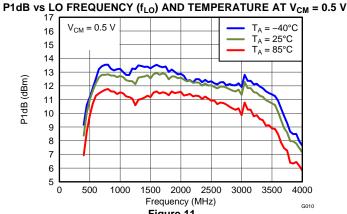


Figure 11.



#### TYPICAL CHARACTERISTICS: Two-Tone Baseband

 $V_{CC} = 3.3 \text{ V}; T_A = +25 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive (LOP)}; I/Q \text{ frequency (f}_{BB}) = 4.5 \text{ MHz}, 5.5 \text{ MHz}; \text{ baseband I/Q}$ amplitude = 0.5-V<sub>PP</sub>/tone differential sine waves in quadrature with  $V_{CM} = 0.25$  V; and broadband output match, unless otherwise noted.

#### OIP3 vs LO FREQUENCY (fLO) AND TEMPERATURE 36 $T_A = -40$ °C 34 $T_A = 25^{\circ}C$ 32 $T_A = 85^{\circ}C$ 30 28 26 24 22 20 18 16 14 12 10 1000 1500 2000 2500 0 500 3000 3500 4000 Frequency (MHz) Figure 12.

#### OIP3 vs LO FREQUENCY (fLO) AND SUPPLY VOLTAGE

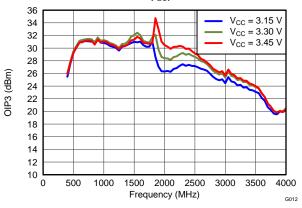
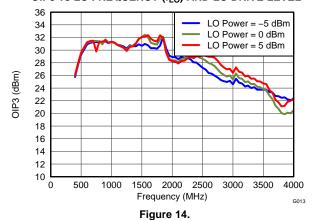
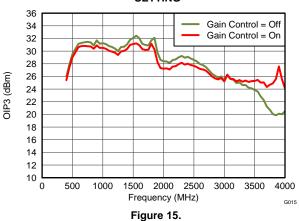


Figure 13.

#### OIP3 vs LO FREQUENCY (fLO) AND LO DRIVE LEVEL



OIP3 vs LO FREQUENCY (fLO) AND GAIN SELECT SETTING



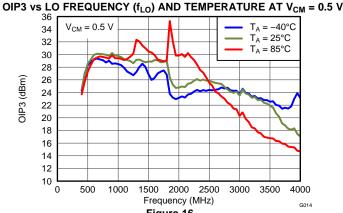
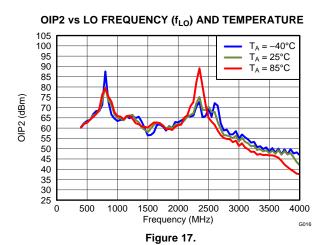


Figure 16.



 $V_{CC} = 3.3 \text{ V}; T_A = +25 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive (LOP)}; I/Q \text{ frequency (f}_{BB}) = 4.5 \text{ MHz}, 5.5 \text{ MHz}; \text{ baseband I/Q}$ amplitude = 0.5-V<sub>PP</sub>/tone differential sine waves in quadrature with V<sub>CM</sub> = 0.25 V; and broadband output match, unless otherwise noted.



OIP2 vs LO FREQUENCY (fLO) AND SUPPLY VOLTAGE

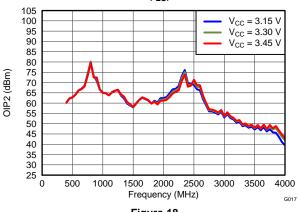
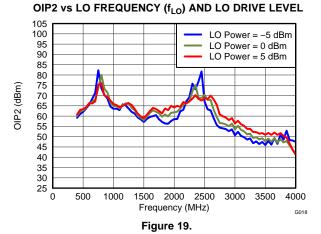
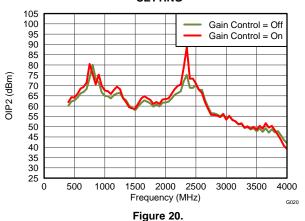


Figure 18.



OIP2 vs LO FREQUENCY ( $f_{LO}$ ) AND GAIN SELECT SETTING



OIP2 vs LO FREQUENCY ( $f_{LO}$ ) AND TEMPERATURE AT  $V_{CM} = 0.5 \text{ V}$ 

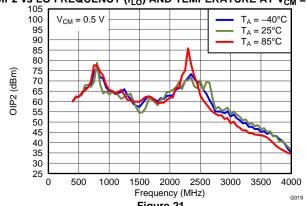


Figure 21.



 $V_{CC} = 3.3 \text{ V}; T_A = +25 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive (LOP)}; I/Q \text{ frequency (f}_{BB}) = 4.5 \text{ MHz}, 5.5 \text{ MHz}; \text{ baseband I/Q}$ amplitude = 0.5- $V_{PP}$ /tone differential sine waves in quadrature with  $V_{CM} = 0.25$  V; and broadband output match, unless otherwise noted.

#### **UNADJUSTED CARRIER FEEDTHROUGH vs LO** FREQUENCY (flo) AND TEMPERATURE

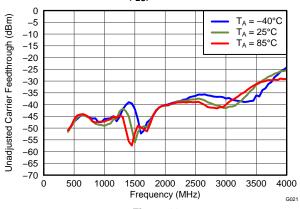


Figure 22.

#### **UNADJUSTED CARRIER FEEDTHROUGH vs LO** FREQUENCY (f<sub>I O</sub>) AND SUPPLY VOLTAGE

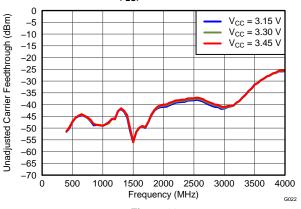


Figure 23.

#### **UNADJUSTED CARRIER FEEDTHROUGH vs LO** FREQUENCY (fLO) AND LO DRIVE LEVEL

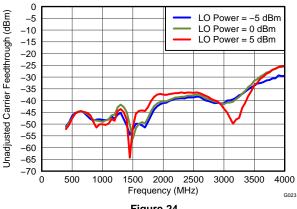


Figure 24.

#### **UNADJUSTED CARRIER FEEDTHROUGH vs LO** FREQUENCY (fLO) AND GAIN SELECT SETTING

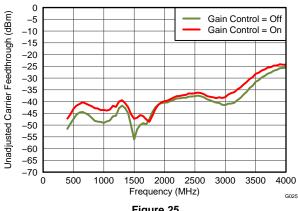
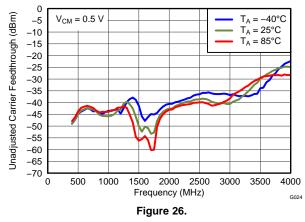


Figure 25.

#### **UNADJUSTED CARRIER FEEDTHROUGH vs LO** FREQUENCY ( $f_{LO}$ ) AND TEMPERATURE AT $V_{CM} = 0.5 \text{ V}$



CARRIER FEEDTHROUGH vs LO FREQUENCY (flo) AND TEMPERATURE AFTER NULLING AT +25°C; MULTIPLE **DEVICES** 

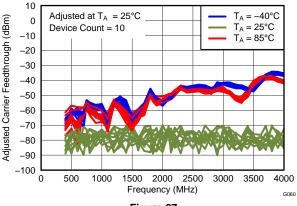


Figure 27.



 $V_{CC} = 3.3 \text{ V}; T_A = +25 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive (LOP)}; I/Q \text{ frequency (f}_{BB}) = 4.5 \text{ MHz}, 5.5 \text{ MHz}; \text{ baseband I/Q}$ amplitude = 0.5- $V_{PP}$ /tone differential sine waves in quadrature with  $V_{CM} = 0.25$  V; and broadband output match, unless otherwise noted.

#### **UNADJUSTED SIDEBAND SUPPRESSION vs LO** FREQUENCY (f<sub>I O</sub>) AND TEMPERATURE

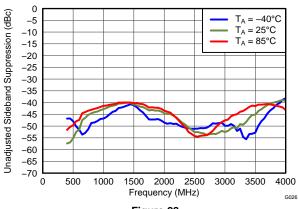


Figure 28.

#### **UNADJUSTED SIDEBAND SUPPRESSION vs LO** FREQUENCY (f<sub>IO</sub>) AND SUPPLY VOLTAGE

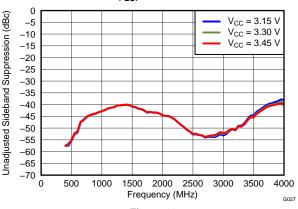


Figure 29.

#### **UNADJUSTED SIDEBAND SUPPRESSION vs LO** FREQUENCY (fLO) AND LO DRIVE LEVEL

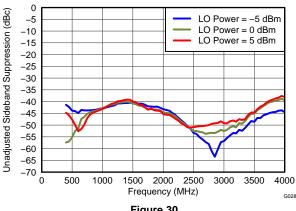


Figure 30.

#### **UNADJUSTED SIDEBAND SUPPRESSION vs LO** FREQUENCY (fLO) AND GAIN SELECT SETTING

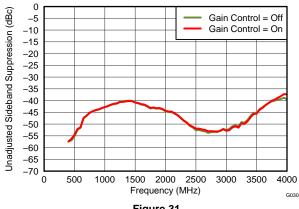
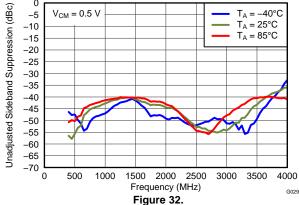


Figure 31.

# UNADJUSTED SIDEBAND SUPPRESSION vs LO FREQUENCY ( $f_{LO}$ ) AND TEMPERATURE AT $V_{CM}$ = 0.5 V

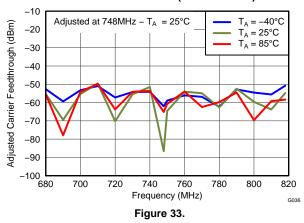




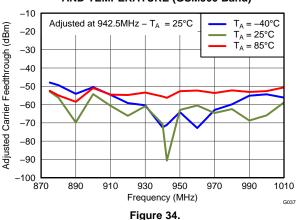
#### TYPICAL CHARACTERISTICS: Two-Tone Baseband, Mid-Band Calibration

 $V_{CC} = 3.3 \text{ V}$ ;  $T_A = +25^{\circ}\text{C}$ ; LO = 0 dBm, single-ended drive (LOP); I/Q frequency ( $f_{BB}$ ) = 4.5 MHz, 5.5 MHz; baseband I/Q amplitude = 0.5- $V_{PP}$ /tone differential sine waves in quadrature with  $V_{CM} = 0.25 \text{ V}$ ; and broadband output match, unless otherwise noted. Single point adjustment mid-band.

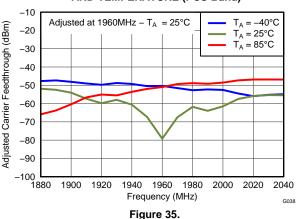
# ADJUSTED CARRIER FEEDTHROUGH vs LO FREQUENCY AND TEMPERATURE (750 LTE Band)



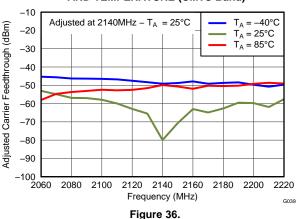
#### ADJUSTED CARRIER FEEDTHROUGH vs LO FREQUENCY AND TEMPERATURE (GSM900 Band)



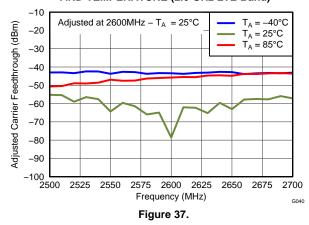
# ADJUSTED CARRIER FEEDTHROUGH vs LO FREQUENCY AND TEMPERATURE (PCS Band)



# ADJUSTED CARRIER FEEDTHROUGH vs LO FREQUENCY AND TEMPERATURE (UMTS Band)



#### ADJUSTED CARRIER FEEDTHROUGH vs LO FREQUENCY AND TEMPERATURE (2.6 GHz LTE Band)



#### ADJUSTED CARRIER FEEDTHROUGH vs LO FREQUENCY AND TEMPERATURE (WiMAX/LTE Band)

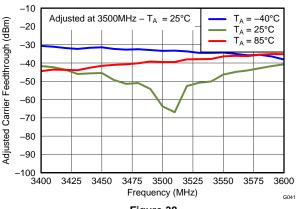


Figure 38.



#### TYPICAL CHARACTERISTICS: Two-Tone Baseband, Mid-Band Calibration (continued)

 $V_{CC} = 3.3 \text{ V}; T_A = +25 ^{\circ}\text{C}; LO = 0 \text{ dBm}, \text{ single-ended drive (LOP)}; I/Q \text{ frequency (f}_{BB}) = 4.5 \text{ MHz}, 5.5 \text{ MHz}; \text{ baseband I/Q}$ amplitude = 0.5- $V_{PP}$ /tone differential sine waves in quadrature with  $V_{CM} = 0.25$  V; and broadband output match, unless otherwise noted. Single point adjustment mid-band.

#### ADJUSTED SIDEBAND SUPPRESSION vs LO FREQUENCY AND TEMPERATURE (750 LTE Band)

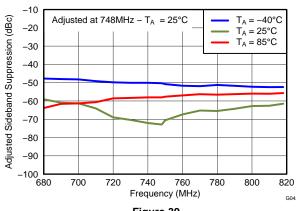


Figure 39.

#### ADJUSTED SIDEBAND SUPPRESSION vs LO FREQUENCY AND TEMPERATURE (GSM900 Band)

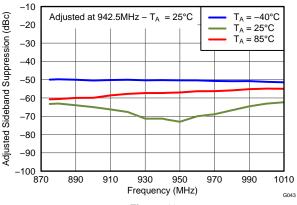


Figure 40.

#### ADJUSTED SIDEBAND SUPPRESSION vs LO FREQUENCY AND TEMPERATURE (PCS Band)

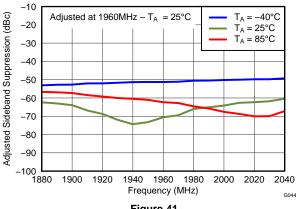


Figure 41.

#### ADJUSTED SIDEBAND SUPPRESSION vs LO FREQUENCY AND TEMPERATURE (UMTS Band)

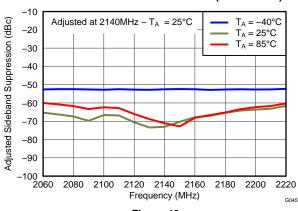


Figure 42.

#### ADJUSTED SIDEBAND SUPPRESSION vs LO FREQUENCY AND TEMPERATURE (2.6 GHz LTE Band)

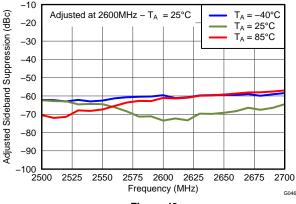


Figure 43.

#### ADJUSTED SIDEBAND SUPPRESSION vs LO FREQUENCY AND TEMPERATURE (WiMAX/LTE Band)

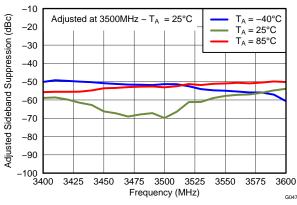
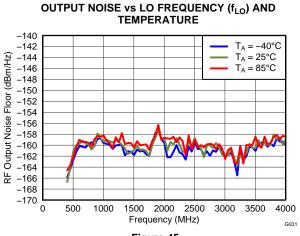


Figure 44.

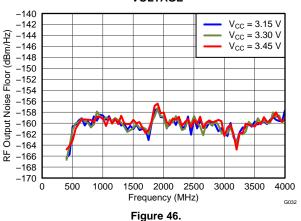


#### TYPICAL CHARACTERISTICS: No Baseband

 $V_{CC}$  = 3.3 V;  $T_A$  = +25°C; LO = 0 dBm, single-ended drive (LOP); and input baseband ports terminated in 50  $\Omega$ , unless otherwise noted.

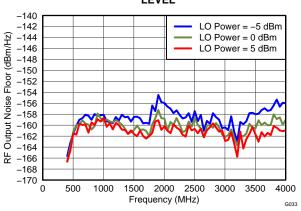


# OUTPUT NOISE vs LO FREQUENCY ( $f_{LO}$ ) AND SUPPLY VOLTAGE



#### Figure 45.

OUTPUT NOISE vs LO FREQUENCY ( $f_{LO}$ ) AND LO DRIVE LEVEL



OUTPUT NOISE vs LO FREQUENCY ( $f_{LO}$ ) AND GAIN SELECT SETTING

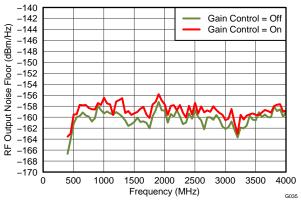
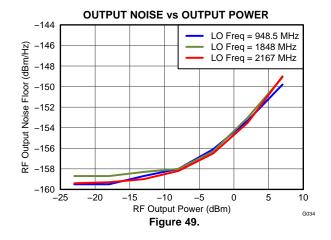


Figure 47.

Figure 48.

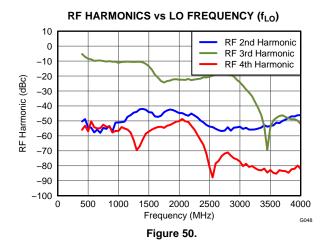


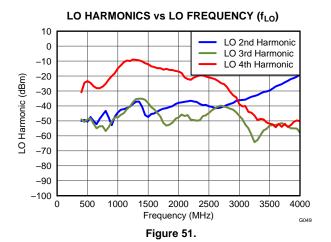
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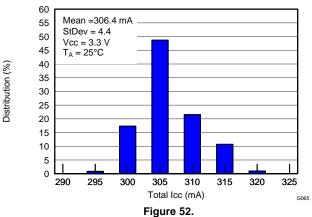
#### TYPICAL CHARACTERISTICS: Two-Tone Baseband

 $V_{CC} = 3.3 \text{ V}$ ;  $T_A = +25^{\circ}\text{C}$ ; LO = 0 dBm, single-ended drive (LOP); I/Q frequency ( $f_{BB}$ ) = 4.5 MHz, 5.5 MHz; baseband I/Q amplitude = 0.5- $V_{PP}$ /tone differential sine waves in quadrature with  $V_{CM} = 0.25 \text{ V}$ ; and broadband output match, unless otherwise noted.





#### NOMINAL CURRENT CONSUMPTION DISTRIBUTION





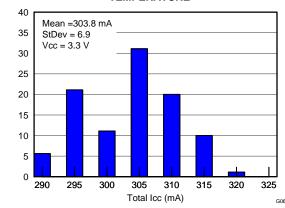
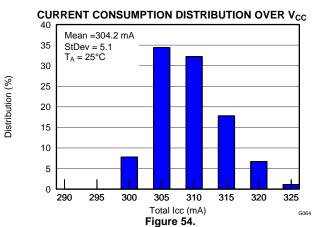


Figure 53.

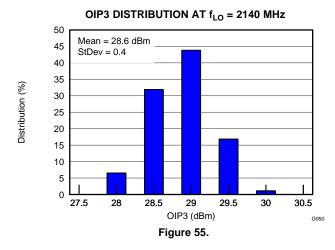
Distribution (%)

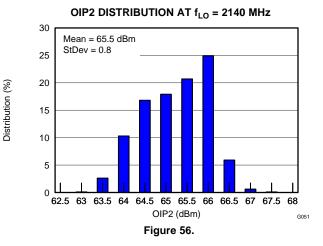


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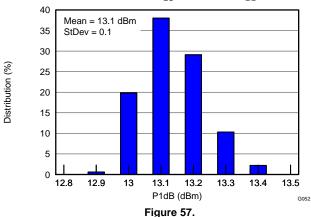


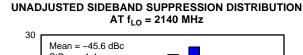
 $V_{CC}$  = 3.3 V;  $T_A$  = +25°C; LO = 0 dBm, single-ended drive (LOP); I/Q frequency (f<sub>BB</sub>) = 4.5 MHz, 5.5 MHz; baseband I/Q amplitude = 0.5-V<sub>PP</sub>/tone differential sine waves in quadrature with V<sub>CM</sub> = 0.25 V; and broadband output match, unless otherwise noted.

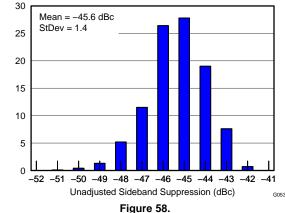




## P1dB DISTRIBUTION AT $f_{LO}$ = 2140 MHz, $f_{BB}$ = 5.5 MHz

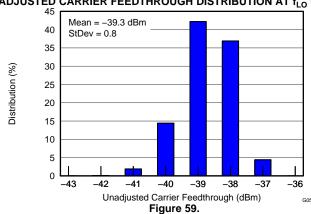






UNADJUSTED CARRIER FEEDTHROUGH DISTRIBUTION AT fLO = 2140 MHz

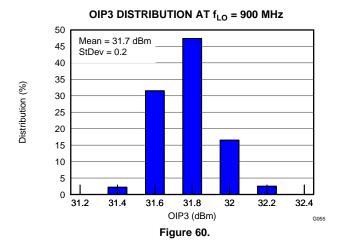
Distribution (%)

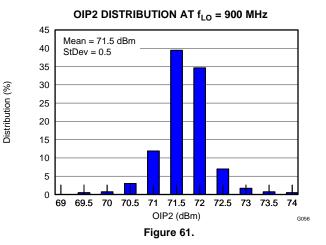


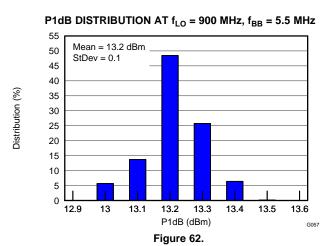
Copyright © 2011, Texas Instruments Incorporated

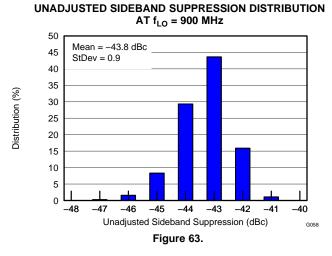


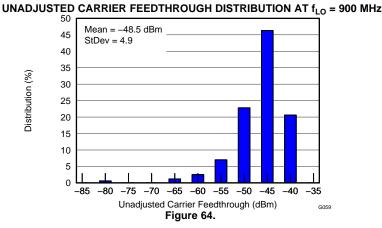
 $V_{CC}$  = 3.3 V;  $T_A$  = +25°C; LO = 0 dBm, single-ended drive (LOP); I/Q frequency (f<sub>BB</sub>) = 4.5 MHz, 5.5 MHz; baseband I/Q amplitude = 0.5-V<sub>PP</sub>/tone differential sine waves in quadrature with V<sub>CM</sub> = 0.25 V; and broadband output match, unless otherwise noted.











Submit Documentation Feedback



#### APPLICATION INFORMATION

#### **Application Schematic**

Figure 65 shows a typical TRF3705 application schematic.

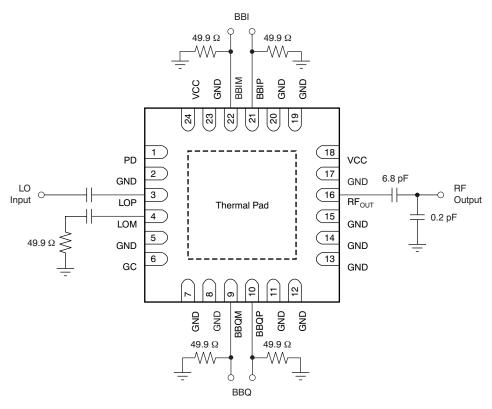


Figure 65. Typical Application Circuit

# **Power Supply and Grounding**

The TRF3705 is powered by supplying a nominal 3.3 V to pins 18 and 24. These supplies can be tied together and sourced from a single clean supply. Proper RF bypassing should be placed close to each power supply pin.

Ground pin connections should have at least one ground via close to each ground pin to minimize ground inductance. The PowerPAD™ must be tied to ground, preferably with the recommended ground via pattern to provide a good thermal conduction path to the alternate side of the board and to provide a good RF ground for the device. (Refer to *PCB Design Guidelines* for additional information.)

#### **Baseband Inputs**

The baseband inputs consist of the in-phase signal (I) and the Quadrature-phase signal (Q). The I and Q lines are differential lines that are driven in quadrature. The nominal drive level is 1-V<sub>PP</sub> differential on each branch.

The baseband lines are nominally biased at 0.25-V common-mode voltage ( $V_{CM}$ ); however, the device can operate with a  $V_{CM}$  in the range of 0 V to 0.5 V. The baseband input lines are normally terminated in 50  $\Omega$ , though it is possible to modify this value if necessary to match to an external filter load impedance requirement.



#### **LO Input**

The LO inputs can be driven either single-ended or differentially. There is no significant performance difference between either option with the exception of the sideband suppression. If driven single-ended, either input can be used, but LOP (pin 3) is recommended for best broadband performance of sideband suppression. When driving in single-ended configuration, simply ac-couple the unused port and terminate in 50  $\Omega$ . The comparison of the sideband suppression performance is shown in Figure 66 for driving the LO single-ended from either pin and for driving the LO input differentially.

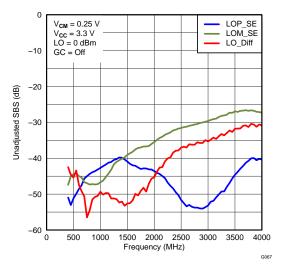


Figure 66. Unadjusted Sideband Suppression (SBS) vs LO Drive Options

### **RF Output**

The RF output must be ac-coupled and can drive a 50- $\Omega$  load. The suggested output match provides the best broadband performance across the frequency range of the device. It is possible to modify the output match to optimize performance within a selected band if needed. The optimized matching circuits are to match the RF output impedances to 50  $\Omega$ .

Figure 67 shows a slightly better OIP3 performance at the frequency above 1850 MHz with an 0.2-pF matching capacitor.

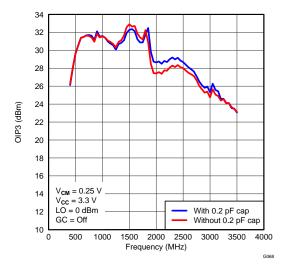


Figure 67. OIP3 with and without a Shunt 0.2-pF Matching Capacitor at the RF Port

22



#### 350-MHz Operation

A different matching circuit, as shown in Figure 68, could also be applied to improve the performance for the frequency from 300 MHz to 400 MHz.

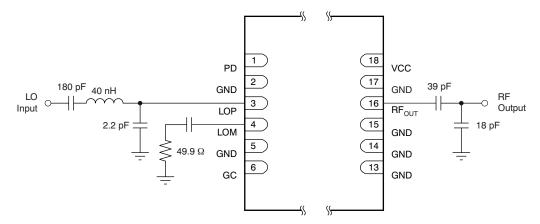
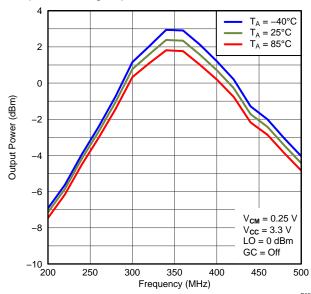


Figure 68. Matching Components for Operation Centered at 350 MHz

Figure 69 and Figure 70 show a slight improvement in OIP3 performance at frequencies above 1850 MHz with an 0.2-pF matching capacitor.



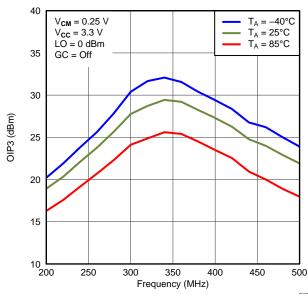


Figure 69. Output Power with 350-MHz Matching Circuit

Figure 70. OIP3 with 350-MHz Matching Circuit



#### DAC to Modulator Interface Network

For optimum linearity and dynamic range, a digital-to-analog converter (DAC) can interface directly with the TRF3705 modulator. It is imperative that the common-mode voltage of the DAC and the modulator baseband inputs be properly maintained. With the proper interface network, the common-mode voltage of the DAC can be translated to the proper common-mode voltage of the modulator. The TRF3705 common-mode voltage is typically 0.25 V, and is ideally suited to interface with the DAC3482/3484 (DAC348x) family because the common-mode voltages of both devices are the same; there is no translation network required. The interface network is shown in Figure 71.

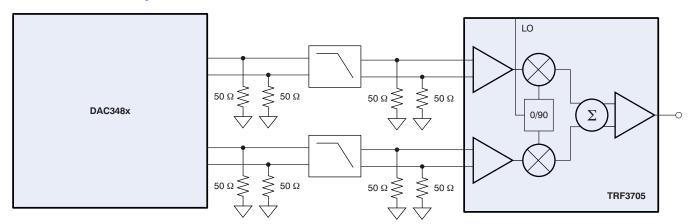


Figure 71. DAC348x Interface with the TRF3705 Modulator

The DAC348x requires a load resistor of 25  $\Omega$  per branch to maintain its optimum voltage swing of 1-V<sub>PP</sub> differential with a 20-mA max current setting. The load of the DAC is separated into two parallel 50- $\Omega$  resistors placed on the input and output side of the low-pass filter. This configuration provides the proper resistive load to the DAC while also providing a convenient 50- $\Omega$  source and load termination for the filter.

#### DAC348x with TRF3705 Modulator Performance

The combination of the DAC348x driving the TRF3705 modulator yields excellent system parameters suitable for high-performance applications. As an example, the following sections illustrate the typical modulated adjacent channel power ratio (ACPR) for common telecom standards and bands. These measurements were taken on the DAC348x evaluation board.



#### **WCDMA**

The adjacent channel power ratio (ACPR) performance using a single-carrier WCDMA signal in the UMTS band is shown in Figure 72.

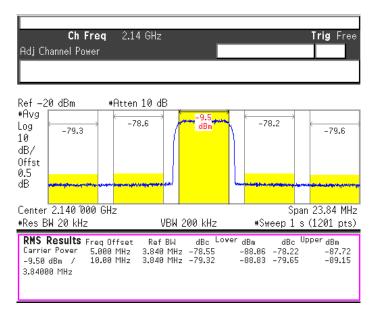


Figure 72. Single-Carrier WCDMA ACPR, IF = 30 MHz, LO Frequency = 2110 MHz

A marginal improvement in OIP3 and output noise performance can be observed by increasing the LO drive power, resulting in slightly improved ACPR performance. The ACPR performance versus LO drive level is plotted in Figure 73 across common frequencies to illustrate the amount of improvement that is possible.

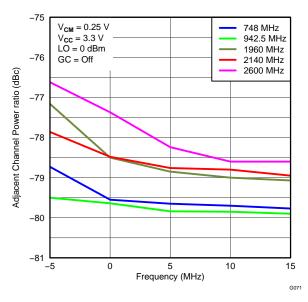


Figure 73. Single-Carrier WCDMA ACPR Performance vs LO Power



#### LTE

ACPR performance using a 10 MHz LTE signal in the 700-MHz band is shown in Figure 74.

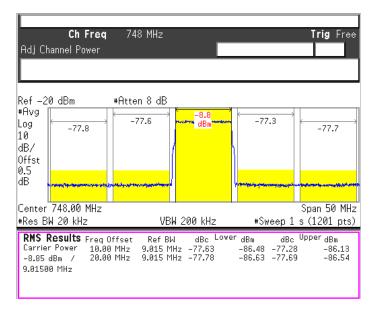


Figure 74. 10 MHz LTE ACPR, IF = 30 MHz, LO Frequency = 718 MHz

#### MC-GSM

ACPR performance using a four-carrier MC-GSM signal in the 1800-MHz band is shown in Figure 75.

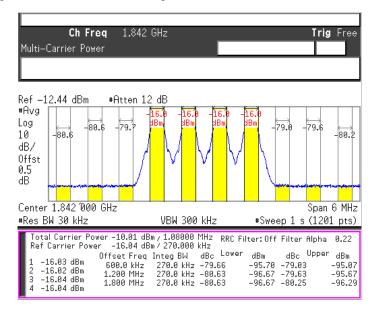


Figure 75. Four-Carrier MC-GSM, IF = 30 MHz ACPR, LO Frequency = 1812 MHz



#### **DEFINITION OF SPECIFICATIONS**

# **Carrier Feedthrough**

This specification measures the power of the local oscillator component that is present at the output spectrum of the modulator. The performance depends on the dc offset balance within the baseband input lines. Ideally, if all of the baseband lines were perfectly matched, the carrier (that is, the LO) would be naturally suppressed; however, small dc offset imbalances within the device allow some of the LO component to feed through to the output. This parameter is expressed as an absolute power in dBm, and is independent of the RF output power and the injected LO input power.

It is possible to adjust the baseband dc offset balance to suppress the output carrier component. Devices such as the DAC348x DAC family have dc offset adjustment capabilities specifically for this function. The Adjusted Carrier Feedthrough graphs (see Figure 33 through Figure 38) optimize the performance at the center of the band at room temperature. Then, with the adjusted dc offset values held constant, the parameter is measured over the frequency band and across the temperature extremes. The typical performance plots provide an indication of how well the adjusted carrier suppression can be maintained over frequency and temperature with only one calibration point.

# **Sideband Suppression**

This specification measures the suppression of the undesired sideband at the output of the modulator relative to the desired sideband. If the amplitude and phase within the I and Q branch of the modulator were perfectly matched, the undesired sideband (or image) would be naturally suppressed. Amplitude and phase imbalance in the I and Q branches result in the increase of the undesired sideband. This parameter is measured in dBc relative to the desired sideband.

It is possible to adjust the relative amplitude and phase balance within the baseband lines to suppress the unwanted sideband. Devices such as the DAC348x DAC family have amplitude and phase adjustment control specifically for this function. The Adjusted Sideband Suppression graphs (refer to Figure 39 through Figure 44) optimize the performance at the center of the band at room temperature. Then, with the adjusted amplitude and phase values held constant, the parameter is measured over the frequency band and across the temperature extremes. The performance plots provide an indication of how well the adjusted sideband suppression can be maintained over frequency and temperature with only one calibration point.

## **Output Noise**

The output noise specifies the absolute noise power density that is output from the RF<sub>OUT</sub> pin (pin 16). This parameter is expressed in dBm/Hz. This parameter, in conjunction with the OIP3 specification, indicates the dynamic range of the device. In general, at high output signal levels the performance is limited by the linearity of the device; at low output levels, on the other hand, the performance is limited by noise. As a result of the higher gain and output power of the TRF3705 compared to earlier devices, it is expected that the noise density is slightly higher as well. With its increased gain and high OIP3 performance, the overall dynamic range of the TRF3705 is maintained at exceptional levels.

Product Folder Link(s): TRF3705



#### **Definition of Terms**

A simulated output spectrum with two tones is shown in Figure 76, with definitions of various terms used in this data sheet.

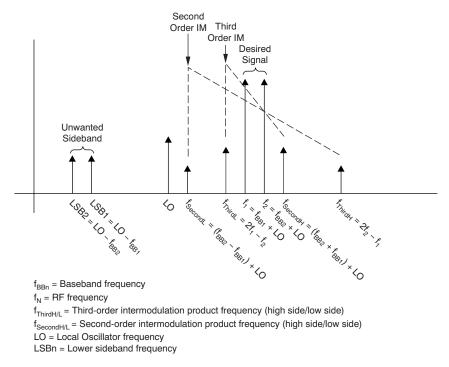


Figure 76. Graphical Illustration of Common Terms

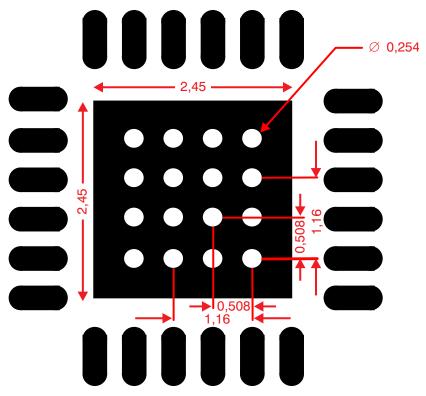


#### **EVALUATION BOARD**

Populated RoHS-compliant evaluation boards are available for testing the TRF3705 as a stand-alone device. Contact your local TI representative for information on ordering these evaluation modules, or see the TRF3705 product folder on the TI website. In addition, the TRF3705 can be evaluated with the DAC348x (quad/dual 16-bit, 1.25GSPS) EVM driving the baseband inputs through a seamless interface at 0.25V common-mode voltage.

#### **PCB Design Guidelines**

The TRF3705 device is fitted with a ground slug on the back of the package that must be soldered to the printed circuit board (PCB) ground with adequate ground vias to ensure a good thermal and electrical connection. The recommended via pattern and ground pad dimensions are shown in Figure 77. The recommended via diameter is 10 mils (0.10 in or 0,25 mm). The ground pins of the device can be directly tied to the ground slug pad for a low-inductance path to ground. Additional ground vias may be added if space allows.



Note: Dimensions are in millimeters (mm).

Figure 77. PCB Ground Via Layout Guide

Decoupling capacitors at each of the supply pins are strongly recommended. The value of these capacitors should be chosen to provide a low-impedance RF path to ground at the frequency of operation. Typically, the value of these capacitors is approximately 10 pF or lower.

The device exhibits symmetry with respect to the quadrature input paths. It is recommended that the PCB layout maintain this symmetry in order to ensure that the quadrature balance of the device is not impaired. The I/Q input traces should be routed as differential pairs and the respective lengths all kept equal to each other. On the RF traces, maintain proper trace widths to keep the characteristic impedance of the RF traces at a nominal 50  $\Omega$ .



#### **Evaluation Board/Kit Important Notice**

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Should this evaluation board/kit not meet the specifications indicated in the User's Guide, the board/kit may be returned within 30 days from the date of delivery for a full refund. THE FOREGOING WARRANTY IS THE EXCLUSIVE WARRANTY MADE BY SELLER TO BUYER AND IS IN LIEU OF ALL OTHER WARRANTIES, EXPRESSED, IMPLIED, OR STATUTORY, INCLUDING ANY WARRANTY OF MERCHANTABILITY OR FITNESS FOR ANY PARTICULAR PURPOSE.

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#### **EVM Warnings and Restrictions**

It is important to operate this EVM within the input voltage range of 0 V to 3.6 V and the output voltage range of 0 V to 3.6 V.

Exceeding the specified input range may cause unexpected operation and/or irreversible damage to the EVM. If there are questions concerning the input range, please contact a TI field representative prior to connecting the input power.

Applying loads outside of the specified output range may result in unintended operation and/or possible permanent damage to the EVM. Please consult the EVM User's Guide prior to connecting any load to the EVM output. If there is uncertainty as to the load specification, please contact a TI field representative.

During normal operation, some circuit components may have case temperatures greater than 55° C. The EVM is designed to operate properly with certain components above 55° C as long as the input and output ranges are maintained. These components include but are not limited to linear regulators, switching transistors, pass transistors, and current sense resistors. These types of devices can be identified using the EVM schematic located in the EVM User's Guide. When placing measurement probes near these devices during operation, please be aware that these devices may be very warm to the touch.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2011, Texas Instruments Incorporated

Product Folder Link(s): TRF3705



# **PACKAGE OPTION ADDENDUM**

11-Apr-2013

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	_	Pins		Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing		Qty	(2)		(3)		(4)	
TRF3705IRGER	ACTIVE	VQFN	RGE	24	3000	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 85	TRF3705 IRGE	Samples
TRF3705IRGET	ACTIVE	VQFN	RGE	24	250	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 85	TRF3705 IRGE	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

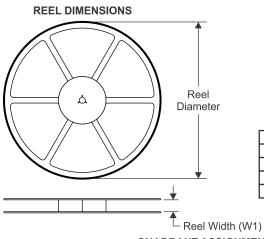
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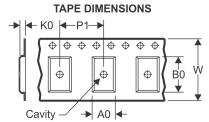
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

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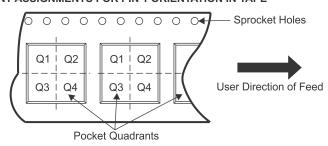
# TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

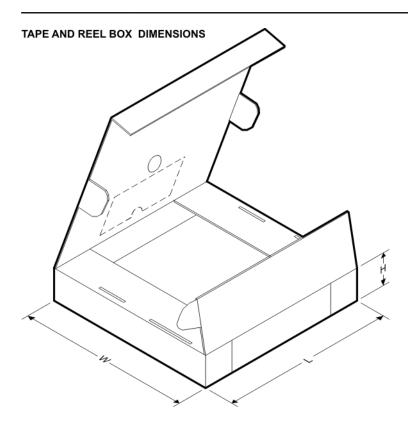
## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

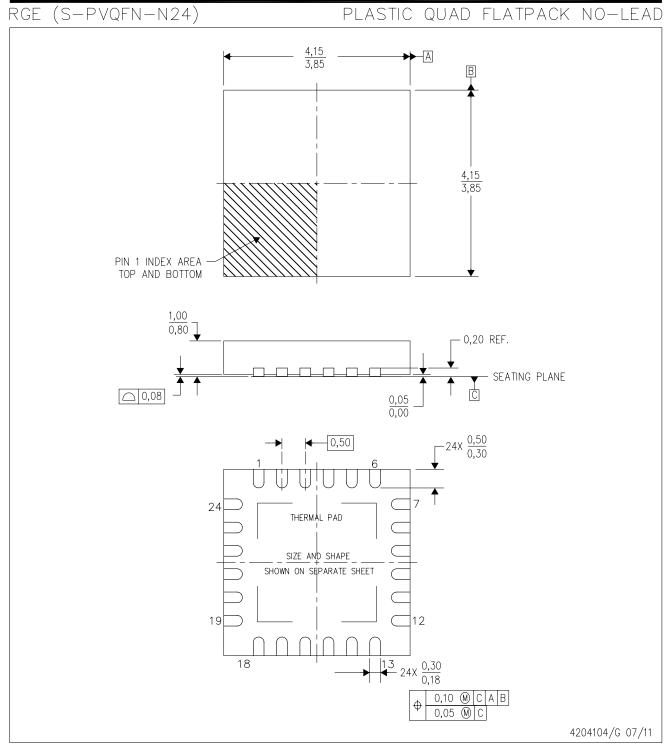
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TRF3705IRGER	VQFN	RGE	24	3000	330.0	12.4	4.3	4.3	1.5	8.0	12.0	Q2
TRF3705IRGET	VQFN	RGE	24	250	180.0	12.4	4.3	4.3	1.5	8.0	12.0	Q2

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#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins SPQ		Length (mm)	Width (mm)	Height (mm)	
TRF3705IRGER	VQFN	RGE	24	3000	338.1	338.1	20.6	
TRF3705IRGET	VQFN	RGE	24	250	210.0	185.0	35.0	



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.

- B. This drawing is subject to change without notice.
- C. Quad Flatpack, No-Leads (QFN) package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F. Falls within JEDEC MO-220.



# RGE (S-PVQFN-N24)

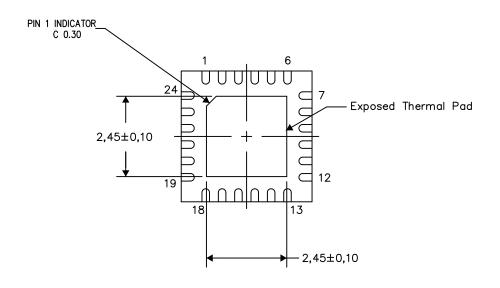
# PLASTIC QUAD FLATPACK NO-LEAD

## THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No—Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View
Exposed Thermal Pad Dimensions

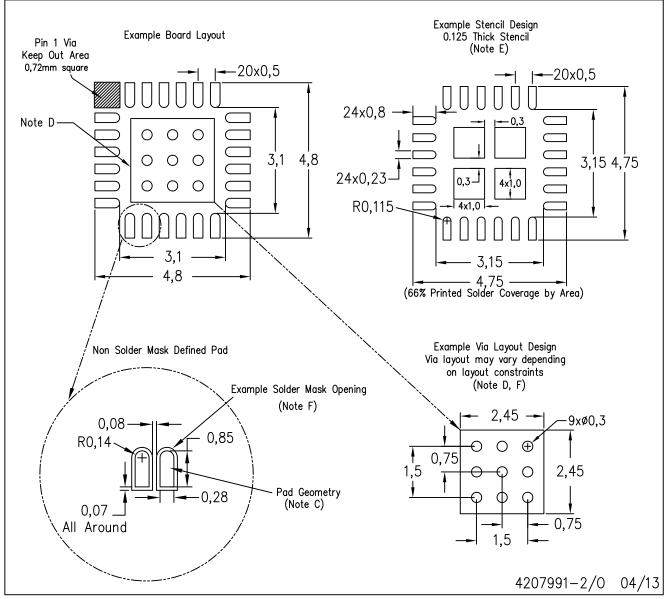
4206344-3/AC 03/13

NOTES: A. All linear dimensions are in millimeters



# RGE (S-PVQFN-N24)

# PLASTIC QUAD FLATPACK NO-LEAD



#### NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat—Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <a href="http://www.ti.com">www.ti.com</a>.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for vias placed in the thermal pad.



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